

SOD-123 Switching Diode 开关二极管**■Features 特点**

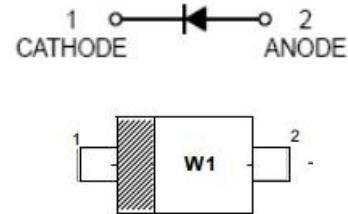
Fast Switching Speed 快的开关速度

Surface mount device 表面贴装器件

High Conductance 高电导率

Case 封装:SOD-123

Marking 印字: W1

**■Maximum Rating 最大额定值**

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Non-Repetitive Peak Reverse Voltage 不重复反向峰值电压	V _{RM}	100	V
DC Reverse Voltage 直流反向电压	V _R	80	V
Forward Rectified Output Current 正向工作电流	I _O	150	mA
Non-Repetitive Peak Surge Current@t=1μS 不重复峰值浪涌电流	I _{FSM}	4	A
Power Dissipation 耗散功率	P _D	400	mW
Thermal Resistance Junction-Ambient 结到环境热阻	R _{θJA}	313	°C/W
Junction/Storage Temperature 结温/储藏温度	T _J , T _{stg}	-50to+150°C	°C

■Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V _R	80		V	I _R =100μA
Forward Voltage 正向电压	V _F	0.62 0.855 1.0 1.25	0.72	V	I _F =5mA I _F =10mA I _F =100mA I _F =150mA
Reverse Current 反向电流	I _R		100 25 50 30	nA nA μA μA	V _R =80V V _R =20V V _R =75V T _J =150°C V _R =20V T _J =150°C
Junction Capacitance 结电容	C _J		4	pF	V _R =0.5V,f=1MHz
Revers Recovery Time 反向恢复时间	T _{rr}		4	nS	I _{rr} = 0.1*I _R , I _F = I _R = 10 mA, R _L = 100Ω

■ Typical Characteristic Curve 典型特性曲线

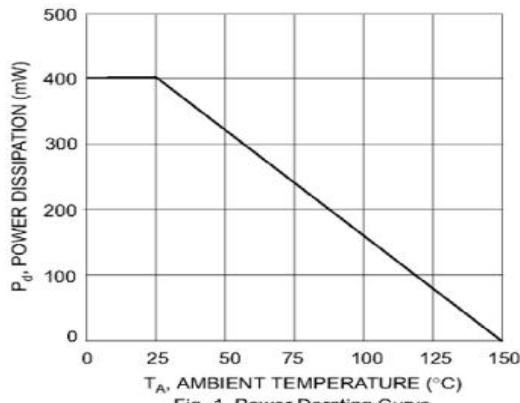


Fig. 1 Power Derating Curve

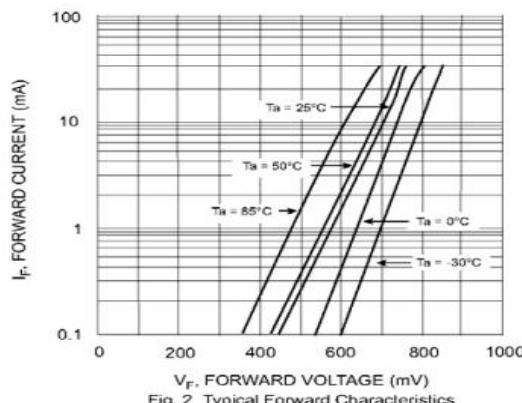


Fig. 2 Typical Forward Characteristics

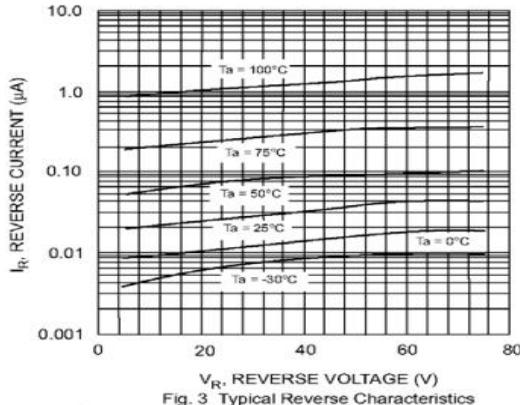


Fig. 3 Typical Reverse Characteristics

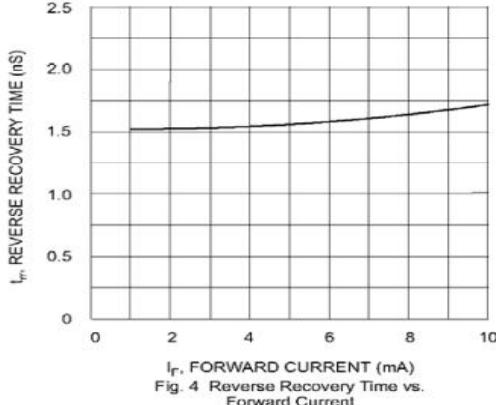
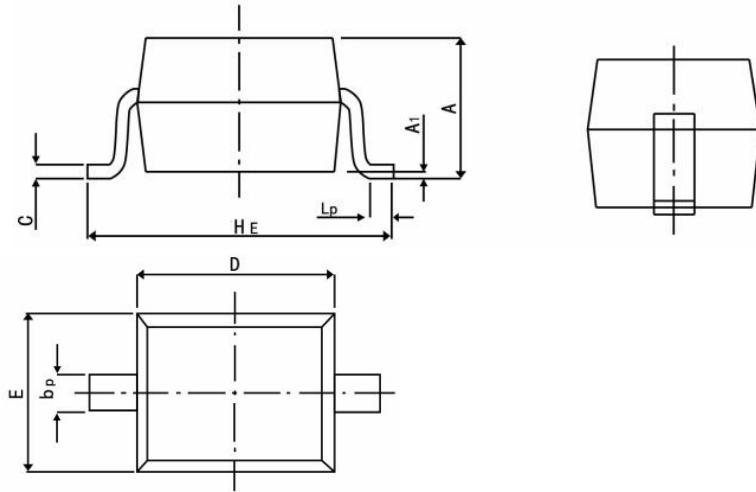


Fig. 4 Reverse Recovery Time vs.
Forward Current

■ Dimension 外形封装尺寸



(mm)	A	bp	C	D	E	H _E	A ₁	L _p
Min	0.9	0.5	0.1	2.55	1.55	3.55	0.01	0.2
Max	1.2	0.6	0.135	2.75	1.65	3.85	0.1	0.5